



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

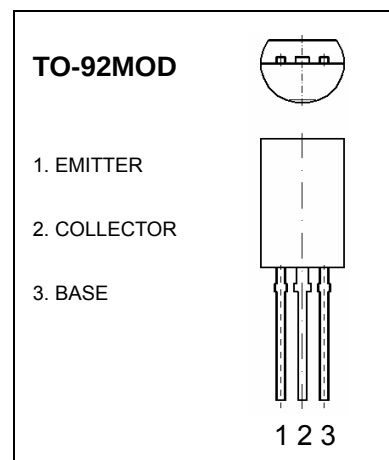
2SB560 TRANSISTOR (PNP)

FEATURES

- High reverse voltage
- Low saturation voltage
- Suitable universal AF power amplifier use

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.7	A
P_C	Collector Power Dissipation	900	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN		MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10 \mu\text{A}$, $I_E = 0$	-100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{ mA}$, $I_B = 0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu\text{A}$, $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20 \text{ V}$, $I_E = 0$			-1	μA
Collector cut-off current	I_{EBO}	$V_{EB} = -4 \text{ V}$, $I_B = 0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5 \text{ V}$, $I_C = -50 \text{ mA}$	60		560	
	$h_{FE(2)}$	$V_{CE} = -5 \text{ V}$, $I_C = -500 \text{ mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$		-0.3	-0.8	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$		-0.85	-1.2	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}$, $I_C = -50 \text{ mA}$		100		MHz
Out capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $f = 1 \text{ MHz}$		15		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	D	E	F	G
Range	60 - 120	100 - 200	160 - 320	280 - 560

Typical Characteristics

2SB56

